

### Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = 25°C
-30V	17mΩ @ V <sub>GS</sub> = -10V	-8.6A
	25mΩ @ V <sub>GS</sub> = -4.5V	-7.1A

### Features and Benefits

- Low R<sub>DS(ON)</sub> – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

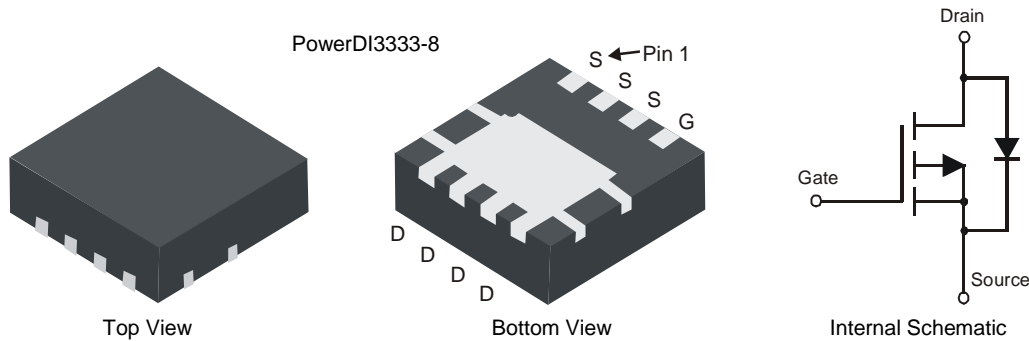
### Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

### Mechanical Data

- Case: PowerDI® 3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.008 grams (Approximate)

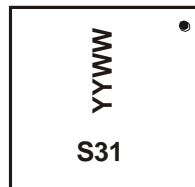


### Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3008SFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMP3008SFGQ-13	PowerDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

### Marking Information



S31 = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last digit of year (ex: 11 = 2011)  
WW = Week code (01 ~ 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-8.6 -7.0	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-11.7 -9.3	A
Continuous Drain Current (Note 7) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-7.1 -5.6	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-9.6 -7.6	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	-80	A
Maximum Continuous Body Diode Forward Current (Note 7)			I <sub>S</sub>	-3.0	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		P <sub>D</sub>	0.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	140	°C/W
	t < 10s		72	°C/W
Total Power Dissipation (Note 7)		P <sub>D</sub>	2.2	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R <sub>θJA</sub>	57	°C/W
	t < 10s		30	°C/W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	7.1	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

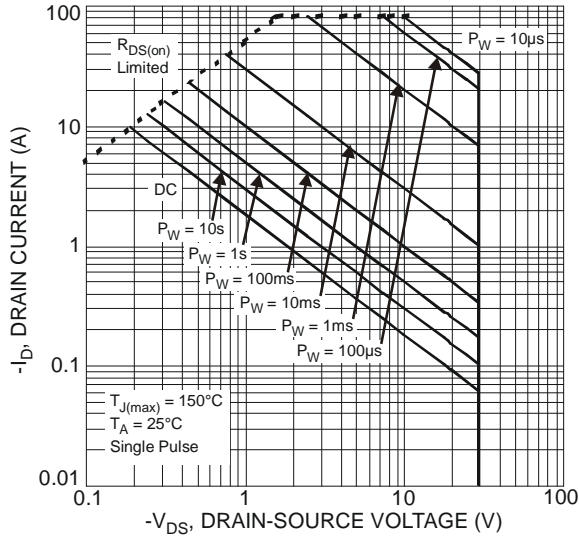


Fig. 1 SOA, Safe Operation Area

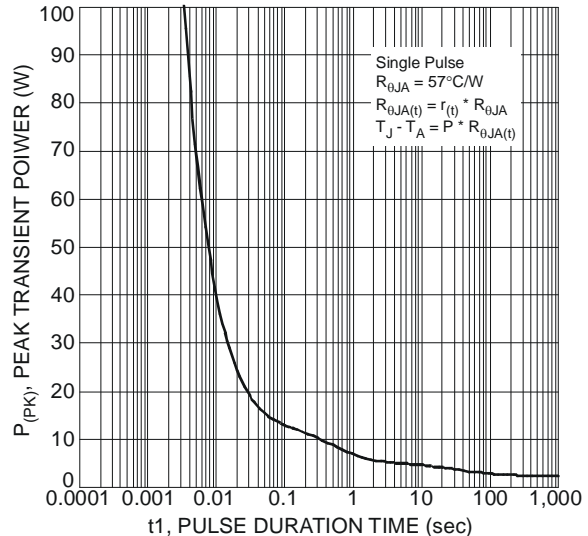


Fig. 2 Single Pulse Maximum Power Dissipation

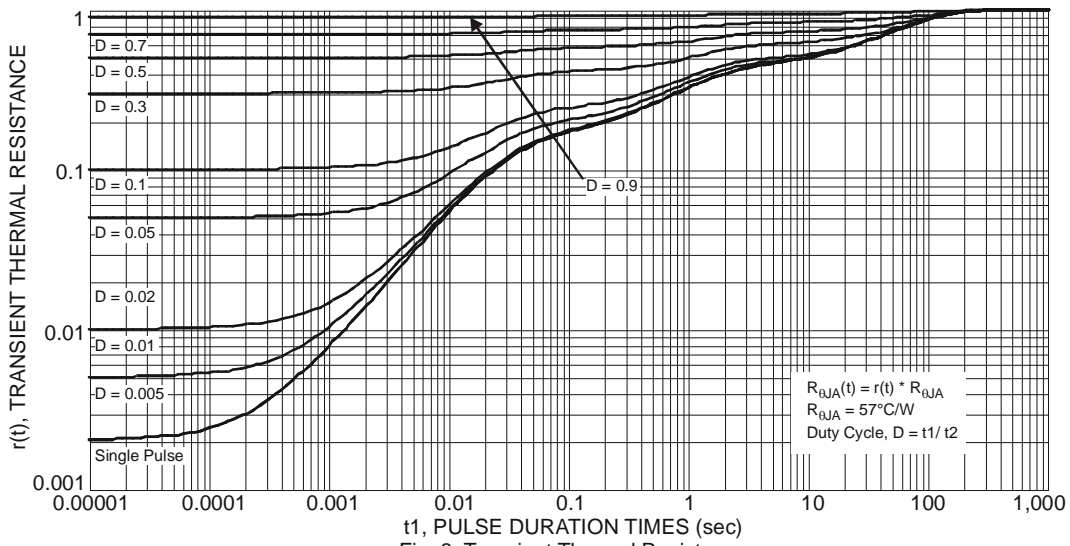


Fig. 3 Transient Thermal Resistance

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-1.0	$\mu A$	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	12.5	17	m $\Omega$	$V_{GS} = -10V, I_D = -10A$
		—	18.5	25		$V_{GS} = -4.5V, I_D = -10A$
Forward Transfer Admittance	$ Y_{fs} $	—	13	—	S	$V_{DS} = -15V, I_D = -10A$
Diode Forward Voltage	$V_{SD}$	—	-0.7	-1.0	V	$V_{GS} = 0V, I_S = -1A$
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	$C_{iss}$	—	2,230	—	pF	$V_{DS} = -15V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	328	—		
Reverse Transfer Capacitance	$C_{rss}$	—	294	—		
Gate Resistance	$R_G$	—	6.4	—	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge ( $V_{GS} = -10V$ )	$Q_g$	—	47	—	nC	$V_{DS} = -15V, I_D = -10A$
Total Gate Charge ( $V_{GS} = -4.5V$ )	$Q_g$	—	23	—		
Gate-Source Charge	$Q_{gs}$	—	9.4	—		
Gate-Drain Charge	$Q_{gd}$	—	5.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	10.5	—	nS	$V_{GS} = -10V, V_{DS} = -15V, R_G = 6\Omega$
Turn-On Rise Time	$t_R$	—	8.5	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	90	—		
Turn-Off Fall Time	$t_F$	—	40	—		

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

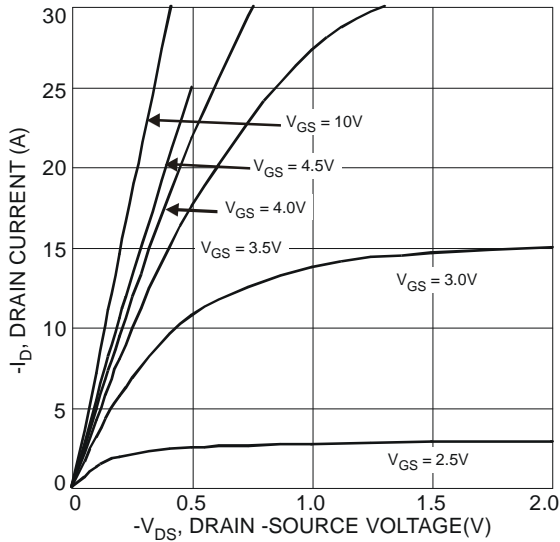


Fig. 4 Typical Output Characteristics

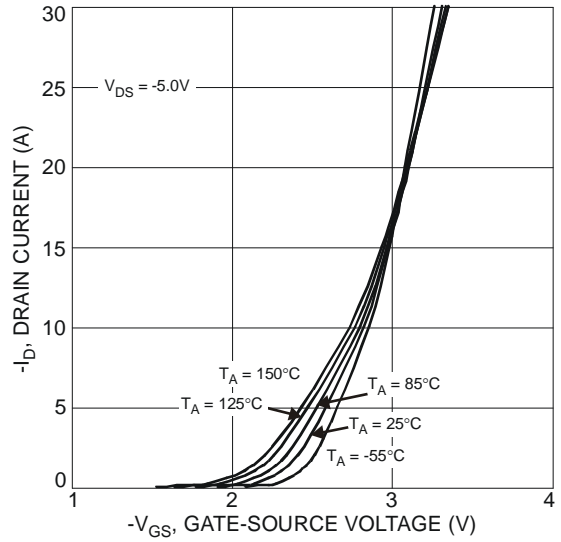


Fig. 5 Typical Transfer Characteristics

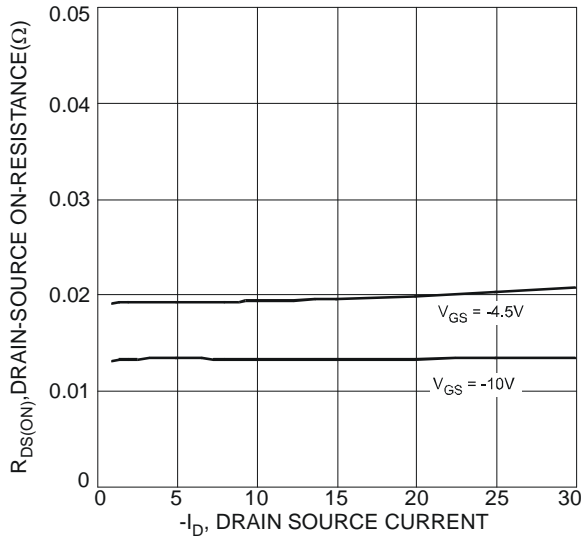


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

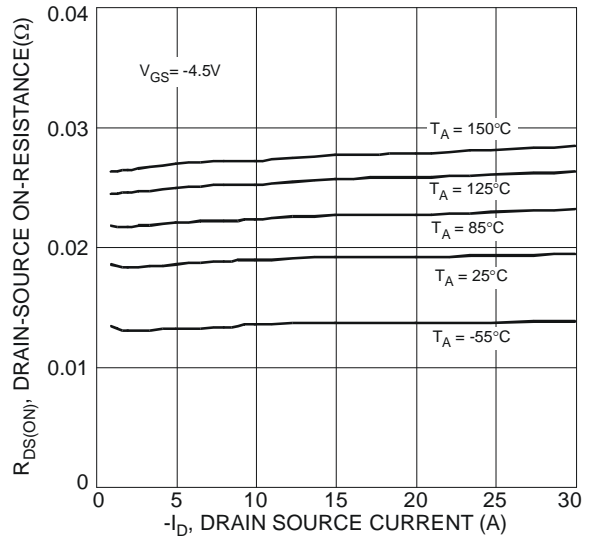


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature

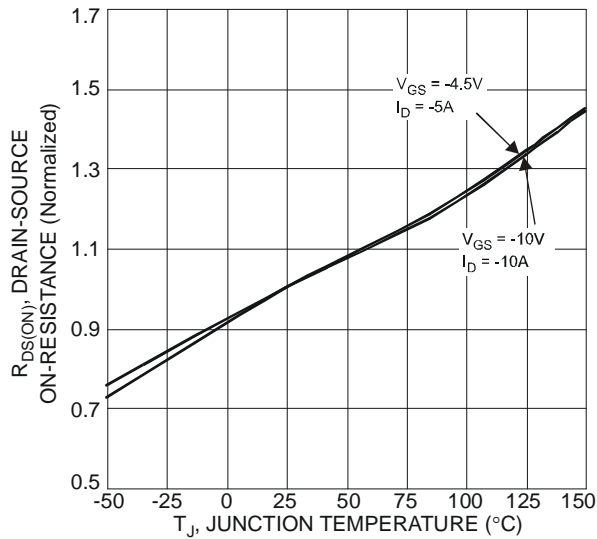


Fig. 8 On-Resistance Variation with Temperature

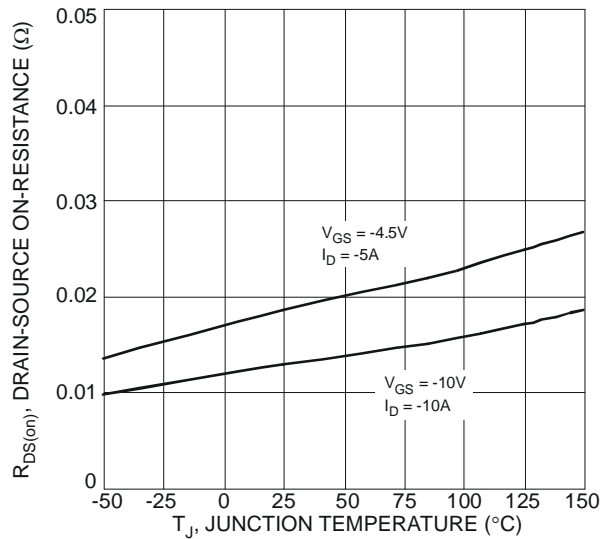


Fig. 9 On-Resistance Variation with Temperature

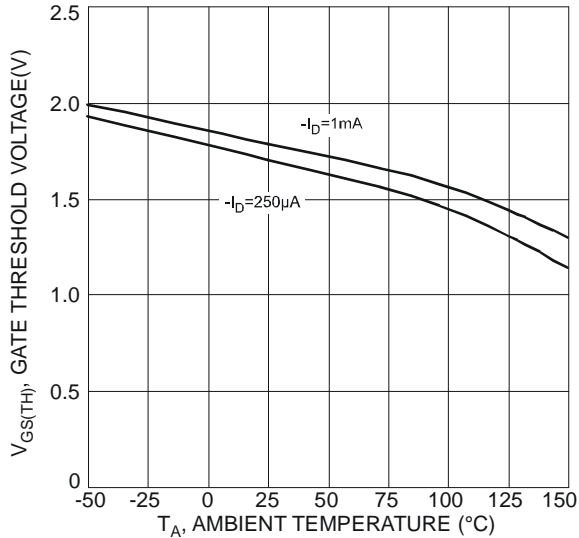


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

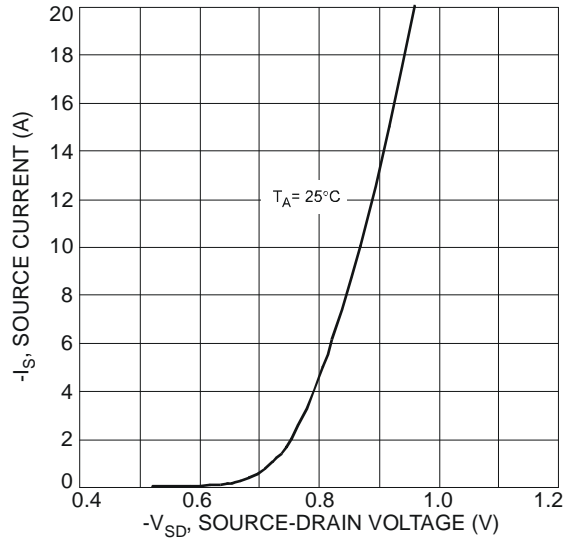


Fig. 11 Diode Forward Voltage vs. Current

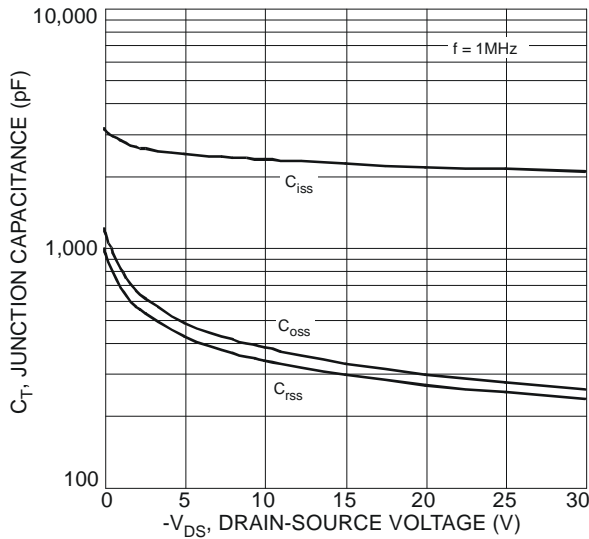


Fig. 12 Typical Junction Capacitance

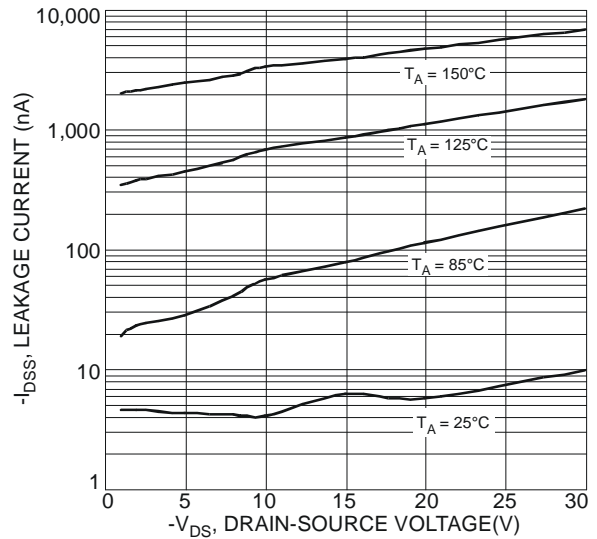


Fig. 13 Typical Drain-Source Leakage Current vs. Voltage

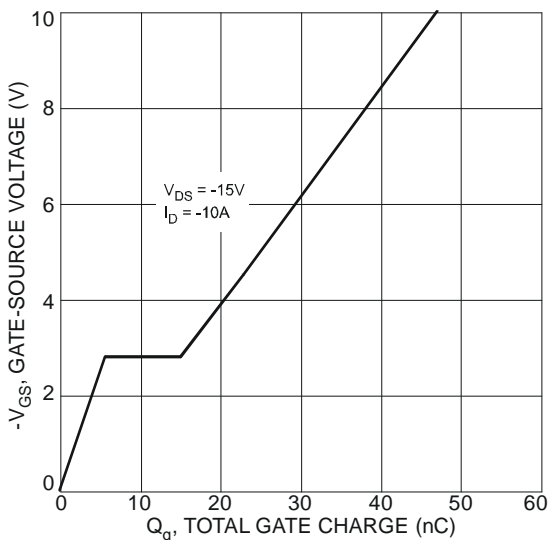
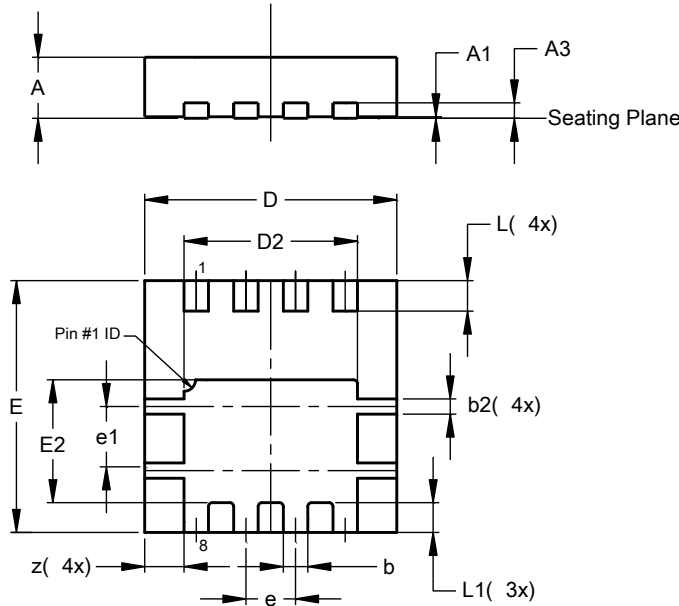


Fig. 14 Gate-Charge Characteristics

**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

**PowerDI3333-8**

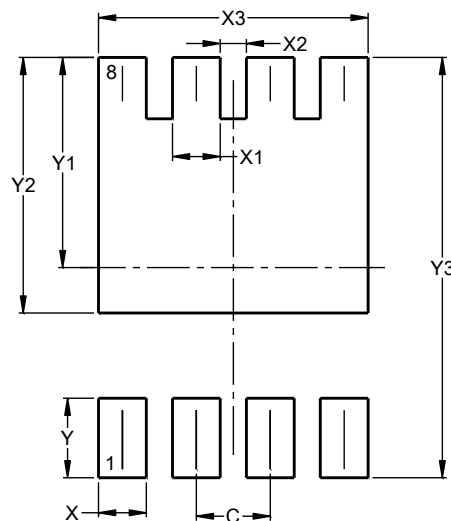


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	-	-	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

**PowerDI3333-8**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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